

Isc N-Channel MOSFET Transistor

IPB200N15N3G

• FEATURES

- With To-263(D2PAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

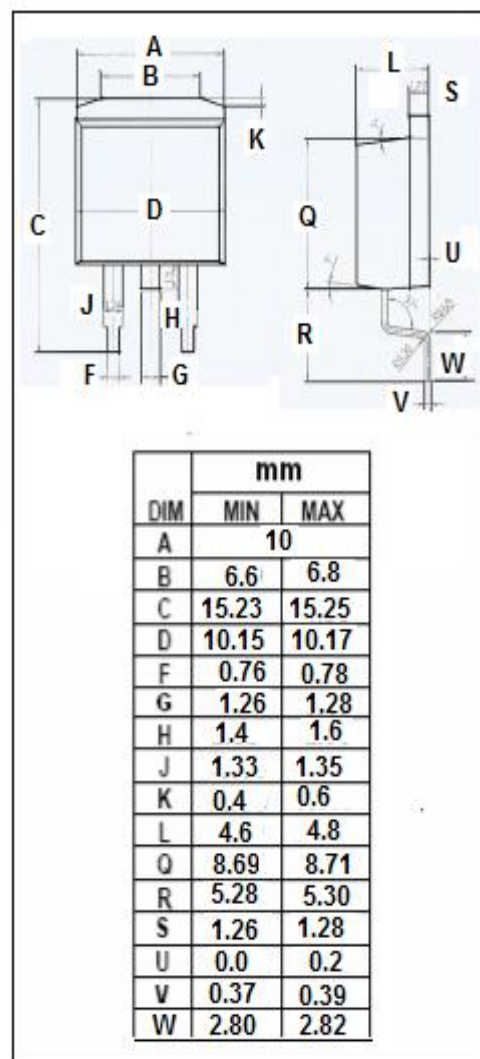
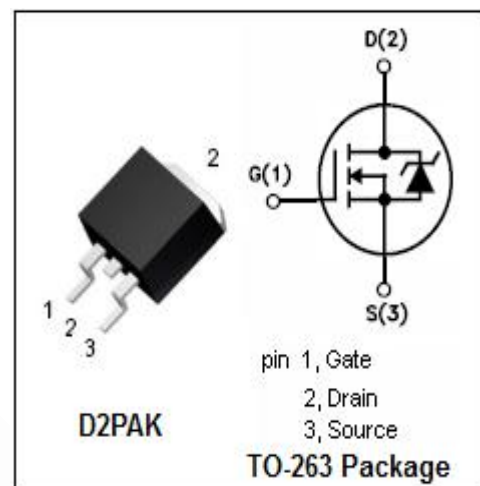
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	50 40	A
I_{DM}	Drain Current-Single Pulsed	200	A
P_D	Total Dissipation @ $T_c=25^{\circ}\text{C}$	150	W
T_{ch}	Max. Operating Junction Temperature	175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	1.0	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	50	$^{\circ}\text{C/W}$



Isc N-Channel MOSFET Transistor**IPB200N15N3G****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1.0mA$	150			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.09mA$	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=50A$		16	20	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=120V; V_{GS}=0V; T_j=25^{\circ}\text{C}$ $V_{DS}=120V; V_{GS}=0V; T_j=125^{\circ}\text{C}$			$\frac{1}{100}$	μA
V_{SDF}	Diode forward voltage	$I_{SD}=50A, V_{GS}=0V$			1.2	V